Abstracts

Accurate Design Centering and Yield Prediction Using the "Truth Model"

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The "Truth Model" is introduced as the first implementation of a statistically validated GaAs FET simulation model. In this paper we examine the power and accuracy of the Truth Model by comparing the predicted and measured statistical response of a GaAs MMIC 0.5 -2.5 GHz amplifier. By design centering a small-signal amplifier both with and without the use of the Truth Model, we show that not only yield estimates are affected by the accuracy of the device statistical model, but also the design center.

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